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Page 4, line 7, please insert the word "a" between "includes" and "method".

Page 4, line 13, please delete the word -the-- between "The" and "step".

Page 6, line 22, please delete the word --an-- and insert the word "a" between "includes" and "deep".

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Page 7, line 8, please delete the word –allow-- and insert the word "allows" between "wall" and "formation".

Page 8, line 15, please delete the label -304-- and insert the label "302" after "n-doped active device region".

IN THE CLAIMS

As indicated below, please AMEND claims 1 and 5.

1. (Twice amended) A semiconductor isolation/structure comprising:

a substrate, the substrate comprising a surface;

a first device and a second device formed within the substrate;

an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:

a deep region which extends into the substrate, the deep region comprising a deep region cross-sectional area;

a shallow region which extends to the surface of the substrate, the shallow region comprising:

a protective outer wall adjacent to the substrate;

an inner sealing wall located <u>exclusively</u> within <u>the shallow region and</u> <u>adjacent to</u> the protective outer wall: and

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the shallow region having a shallow region cross-sectional area; wherein

the deep region cross-sectional area is greater than the shallow region.

cross-sectional area.

5. (Twice amended) A semiconductor isolation structure comprising:

a substrate, the substrate comprising a surface;

a first device and a second device formed within the substrate;

an isolation region formed within the substrate between the first device and the second device, the isolation region comprising;

a deep region which extends into the substrate, the deep region comprising an oxide;

a shallow region which extend to the surface of the substrate, the shallow region comprising:

a protective outer wall adjacent to the substrate,

an inner sealing wall located <u>exclusively</u> within <u>the shallow region and</u> <u>adjacent to</u> the protective outer wall.

REMARKS

Claims 1, 2 and 4-6 are pending. Claim 3 has been previously canceled. The Specification has been amended to correct some egregious typographical errors. Claims 1 and 5 have also been amended. No new matter was added when making the amendments to the specification or claims.

Rejected Claims - 35 U.S.C. 112, first paragraph

The Office Action stated that Claims 1, 2 and 4-6 stand rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in